



SHEET 1 OF 1

| FORM PTO - 1449 SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT | | | | | ATTY DOCKET NO.: ASC-023DVC2 APPLICANT: Fitzgerald SERIAL NO.: 10/022,689 FILING DATE: December 17, 2001 GROUP: 2813 | | | | |
|--|--|--------------------|------------|-----------------|---|--------------|-------------------------------|------------------|--------------------------|
| U.S. PATENT DOCUMENTS | | | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE | | |
| <i>car</i> | A117 | 5,424,243 | 06/13/1995 | Takasaki | | | | | |
| <i>car</i> | A118 | 2002/0052084 | 05/02/2002 | Fitzgerald | | | 05/16/2001 | | |
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| <i>car</i> | A120 | 6,602,613 | 08/05/2003 | Fitzgerald | | | 01/17/2001 | | |
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| FOREIGN PATENT DOCUMENTS | | | | | | | | | |
| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
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| OTHER ART, JOURNAL ARTICLES, ETC. | | | | | | | | | |
| EXAM. INIT. | OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) | | | | | | | | |
| | <i>TO 2000 MAIL ROOM FEE PAID</i> | | | | | | | | |
| | <i>AUG 29 2001</i> | | | | | | | | |
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| | <i>MAIL ROOM FEE PAID</i> | | | | | | | | |
| EXAMINER | <i>Whitehead</i> | | | | | | | | |
| | DATE CONSIDERED <i>2003</i> | | | | | | | | |

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| FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP (Rev. 5/92) 225 Franklin Street, Boston, MA 02110 Telephone: (617) 426-9180 | MIT7759DIVCON ATTORNEY DOCKET NO. Eugene A. Fitzgerald APPLICANT Herewith FILING DATE | Unknown SERIAL NO. Unknown GROUP Unknown EXAMINER |
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| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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| COT | AA | 5,177,583 | January 5, 1993 | Endo et al. | 257 | 190 | January 10, 1991 |
| | AB | 5,298,452 | March 29, 1994 | Meyerson | 437 | 81 | February 21, 1992 |
| | AC | 5,630,905 | May 20, 1997 | Lynch et al. | 438 | 507 | June 5, 1995 |
| | AD | 5,906,951 | May 25, 1999 | Chu et al. | 438 | 751 | April 30, 1997 |
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| | AF | 5,891,769 | April 6, 1999 | Liaw et al. | 438 | 167 | February 27, 1998 |
| | AG | 5,714,777 | February 3, 1998 | Ismail et al. | 257 | 263 | February 19, 1997 |
| | AH | 5,534,713 | July 9, 1996 | Ismail et al. | 257 | 24 | May 20, 1994 |
| | AI | 5,250,445 | October 5, 1993 | Bean et al. | 437 | 11 | January 17, 1992 |
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| | AL | 5,399,522 | March 21, 1995 | Ohori | | | September 8, 1993 |
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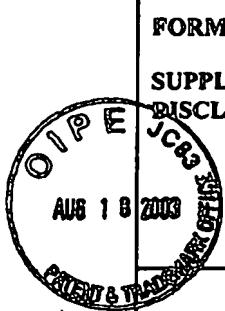
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| EXAMINER INITIAL | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES NO |
|------------------|----|-----------------|----------|---------|-------|----------|--------------------|
| COT | AN | 0 514 018 A2 | 16.04.92 | EPO | | | |
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| | AP | | | | | | |

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| Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | |



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| EXAM. INIT. | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB CLASS | FILING DATE IF APPROPRIATE |
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| | A4 | 4,990,979 | 02/05/1991 | Otto | | | |
| | A5 | 5,013,681 | 05/07/1991 | Godbey et al. | | | |
| | A6 | 5,155,571 | 10/13/1992 | Wang et al. | | | |
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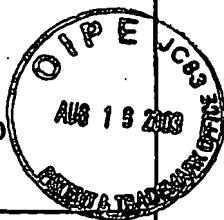
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| EXAMINER <i>hannah Schlegel</i> DATE CONSIDERED <i>8/4/04</i> | | | | | | | | |



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| EXAMINER <i>Maressa Schutz</i> | | | | DATE CONSIDERED <i>8/4/04</i> | | | |



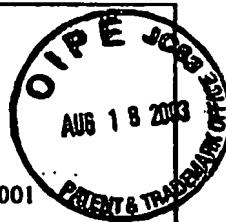
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| | A98 | 6,429,061 | 08/06/2002 | Rim | | | 07/26/2000 |
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| EXAMINER | <i>Waseem Saleem</i> | DATE CONSIDERED | <i>8/4/04</i> |
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| EXAM. INIT. | | DOCUMENT NUMBER | DATE | COUNTRY CODE | CLASS | SUB CLASS | FILING DATE | ABSTRACT ONLY | ENGLISH LANG (Y/N) |
| | B1 | 41 01 167 | 07/23/1992 | DE | | | | NO | NO |
| | B2 | 0 587 520 | 03/16/1994 | EP | | | | NO | YES |
| | B3 | 0 683 522 | 11/22/1995 | EP | | | | NO | YES |
| | B4 | 0 828 296 | 03/11/1998 | EP | | | | NO | YES |
| | B5 | 0 829 908 | 03/18/1998 | EP | | | | NO | YES |
| | B6 | 0 838 858 | 04/29/1998 | EP | | | | NO | NO |
| | B7 | 1 020 900 | 07/19/2000 | EP | | | | NO | YES |
| | B8 | 1 174 928 | 01/23/2002 | EP | | | | NO | YES |
| | B9 | 2 342 777 | 04/19/2000 | GB | | | | YES | YES |
| | B10 | 10-270685 | 10/09/1998 | JP | | | | NO | YES |
| | B11 | 11-233744 | 08/27/1999 | JP | | | | NO | NO |
| | B12 | 2000-021783 | 08/31/2000 | JP | | | | NO | YES |
| | B13 | 2000-031491 | 01/28/2000 | JP | | | | NO | NO |
| | B14 | 2001-319935 | 11/16/2001 | JP | | | | NO | YES |
| | B15 | 2002-076334 | 03/15/2002 | JP | | | | NO | YES |
| | B16 | 2002-164520 | 06/07/2002 | JP | | | | NO | YES |
| | B17 | 2002-289533 | 10/04/2002 | JP | | | | NO | YES |
| | B18 | 4-307974 | 10/30/1992 | JP | | | | NO | NO |
| | B19 | 5-166724 | 07/02/1993 | JP | | | | NO | Abstract Only |
| | B20 | 6-177046 | 06/24/1994 | JP | | | | NO | Abstract Only |
| | B21 | 7-106446 | 04/21/1995 | JP | | | | NO | NO |
| | B22 | 7-240372 | 09/12/1995 | JP | | | | NO | Abstract Only |
| | B23 | 00/48239 | 08/17/2000 | WO | | | | NO | YES |
| | B24 | 00/54338 | 09/14/2000 | WO | | | | NO | YES |

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| EXAMINER | <i>Helen Schulyer</i> | DATE CONSIDERED | 8/4/04 |
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|----------------|-----|--------------------|------------|-----------------|-------|--------------|----------------|------------------|-----------------------|
| | B25 | 01/022482 | 03/29/2001 | WO | | | | NO | YES |
| | B26 | 01/54202 | 07/26/2001 | WO | | | | NO | YES |
| | B27 | 01/93338 | 12/06/2001 | WO | | | | NO | YES |
| | B28 | 01/99169 | 12/27/2001 | WO | | | | NO | YES |
| | B29 | 02/071488 | 09/12/2002 | WO | | | | NO | YES |
| | B30 | 02/071491 | 09/12/2002 | WO | | | | NO | YES |
| | B31 | 02/071495 | 09/12/2002 | WO | | | | NO | YES |
| | B32 | 02/082514 | 10/17/2002 | WO | | | | NO | YES |
| | B33 | 02/13262 | 02/14/2002 | WO | | | | NO | YES |
| | B34 | 02/15244 | 02/21/2002 | WO | | | | NO | YES |
| | B35 | 02/27783 | 04/04/2002 | WO | | | | NO | YES |
| | B36 | 02/47168 | 06/13/2002 | WO | | | | NO | YES |
| | B37 | 98/59365 | 12/30/1998 | WO | | | | NO | YES |
| | B38 | 99/53539 | 10/21/1999 | WO | | | | NO | YES |
| | B39 | 6-252046 | 11/19/1992 | JP | | | | NO | YES |

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| EXAMINER | <i>hannah Schuyler</i> | DATE CONSIDERED | 8/4/04 |
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| | C2 | Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices", PhD Thesis, Massachusetts Institute of Technology, 1999, pp. 1-154. |
| | C3 | Augusto et al., "Proposal for a New Process Flow for the Fabrication of Silicon-based Complementary MOD-MOSFETs without ion Implantation," Thin Solid Films, vol. 294, no. 1-2, pp. 254-258 (February 15, 1997). |
| | C4 | Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," Modern Physics Letters B (2001) (abstract). |
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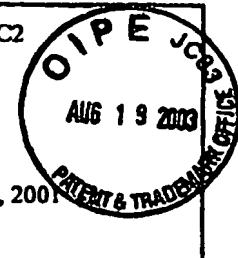
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